

Product data sheet

1. General description

High voltage high speed planar passivated NPN power switching transistor in a SOT428 (DPAK) surface mountable plastic package.

2. Features and benefits

- Fast switching
- Low thermal resistance
- Surface mountable package
- Tight DC gain spreads
- Very high voltage capability
- Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- High frequency electronic lighting ballasts
- Inverters
- Motor control systems

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CM}	peak collector current	Fig. 1; Fig. 2; Fig. 3	-	-	10	А
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 4</u>	-	-	80	W
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	1050	V
Static chara	acteristics	· · · · ·				
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12	28	34	47	
		I_{C} = 250 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12	35	43	57	
		I _C = 800 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12	31	37	48	

5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	В	base	[]	С			
2	С	collector[1]		в			
3	Е	emitter					
mb	С	mounting base; connected to collector		E sym123			
			DPAK (SOT428)				

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
BUJ303CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428					

7. Marking

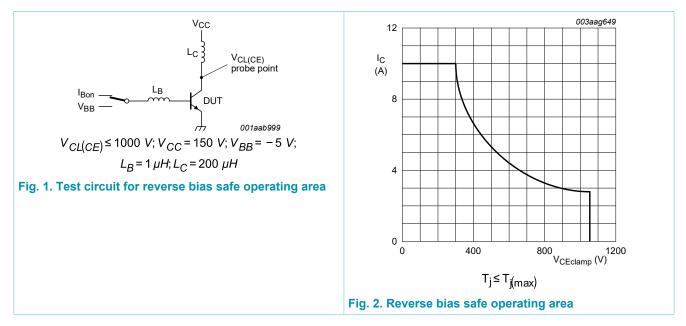
Table 4. Marking codes					
Type number	Marking code				
BUJ303CD	BUJ303CD				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	1050	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
I _C	collector current	Fig. 1; Fig. 2; Fig. 3	-	5	А
I _{CM}	peak collector current		-	10	А
I _B	base current		-	2	А
I _{BM}	peak base current		-	4	А
P _{tot}	total power dissipation	$T_{mb} \leq 25 \text{ °C}; \underline{Fig. 4}$	-	80	W
T _{stg}	storage temperature		-65	150	°C
Тј	junction temperature		-	150	°C



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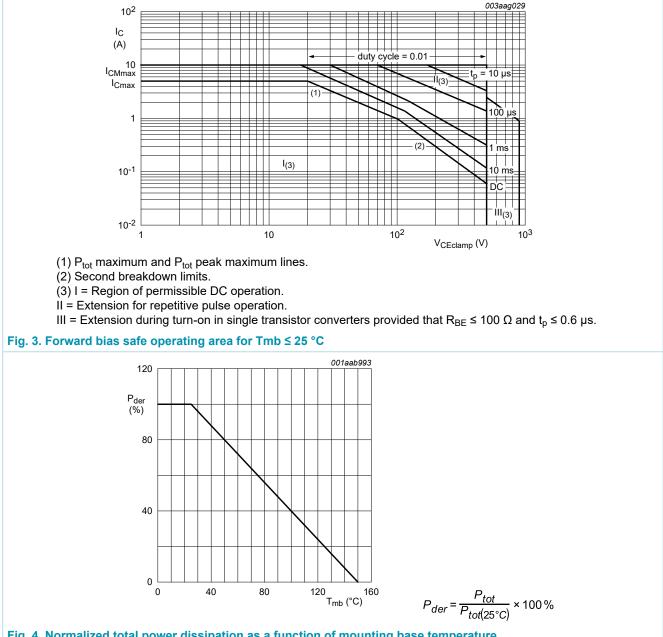
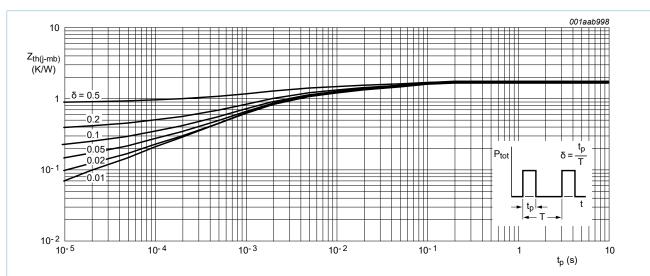


Fig. 4. Normalized total power dissipation as a function of mounting base temperature

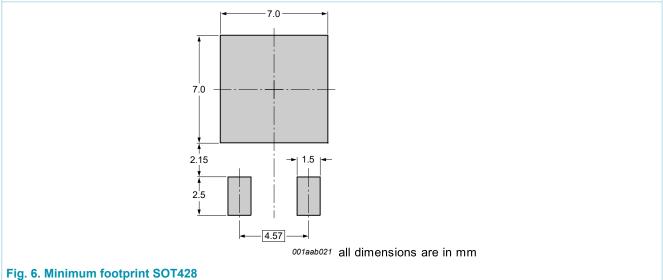
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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint; <u>Fig. 6</u>		-	75	-	K/W







10. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static char	acteristics	·					-
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 1050 V	[1]	-	-	1	mA
	current (base shorted)	V _{BE} = 0 V; V _{CE} = 1050 V; T _j = 125 °C	[1]	-	-	2	mA
I _{CBO}	collector-base cut-off current (emitter open)	V _{CB} = 1050 V; I _E = 0 A; T _{mb} = 25 °C	[1]	-	-	1	mA
I _{CEO}	collector-emitter cut-off current (base open)	V_{CE} = 400 V; I _B = 0 A; T _{mb} = 25 °C	[1]	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current (collector open)	V_{EB} = 9 V; I _C = 0 A; T _{mb} = 25 °C		-	-	0.1	mA
V _{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 100 \text{ mA}; L_C = 25 \text{ mH};$ $T_{mb} = 25 \text{ °C}; Fig. 7; Fig. 8$		400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	I _C = 1 A; I _B = 0.2 A; T _{mb} = 25 °C; <u>Fig. 9;</u> <u>Fig. 10</u>		-	-	0.5	V
		I _C = 3 A; I _B = 1 A; T _{mb} = 25 °C; <u>Fig. 9;</u> <u>Fig. 10</u>		-	0.25	1.5	V
V _{BEsat}	base-emitter saturation voltage	I _C = 3 A; I _B = 1 A; T _{mb} = 25 °C; <u>Fig. 11</u>		-	1	1.5	V
h _{FE}	DC current gain	I_{C} = 10 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12		28	34	47	
		I _C = 250 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12		35	43	57	
		I _C = 800 mA; V _{CE} = 3 V; T _{mb} = 25 °C; Fig. 12		31	37	48	
Dynamic cl	naracteristics (switching tir	nes - resistive load)	,				
t _{on}	turn-on time	I _C = 2.5 A; I _{Bon} = 0.5 A; I _{Boff} = -1 A;		-	1	-	ms
t _s	storage time	R _L = 100 Ω; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	2.5	-	ms
t _f	fall time			-	0.3	-	ms
Dynamic cl	naracteristics (switching tir	nes - inductive load)					
t _s	storage time	I_{C} = 2.5 A; I_{Bon} = 0.5 A; V_{BB} = -5 V; L_{B} = 1 µH; T_{j} = 25 °C; Fig. 15; Fig. 16		-	2	-	ms
		$ I_{C} = 2.5 \text{ A}; I_{Bon} = 0.5 \text{ A}; V_{BB} = -5 \text{ V}; L_{B} = 1 \ \mu\text{H}; T_{j} = 100 \ ^{\circ}\text{C}; \underline{\text{Fig. 15}}; \underline{\text{Fig. 16}} $		-	3	-	ms
t _f	fall time	$ I_{C} = 2.5 \text{ A}; \ I_{Bon} = 0.5 \text{ A}; \ V_{BB} = -5 \text{ V}; \\ L_{B} = 1 \ \mu \text{H}; \ T_{j} = 25 \ ^{\circ}\text{C}; \ \underline{\text{Fig. 15}}; \ \underline{\text{Fig. 16}} $		-	200	-	ns
		I _C = 2.5 A; I _{Bon} = 0.5 A; V _{BB} = -5 V; L _B = 1 μH; T _i = 100 °C; <u>Fig. 15; Fig. 16</u>		-	300	-	ns

[1] Measured with half-sine wave voltage (curve tracer).

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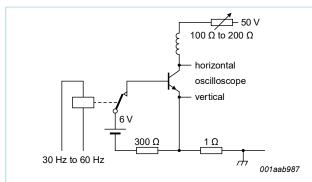


Fig. 7. Test circuit for collector-emitter sustaining voltage

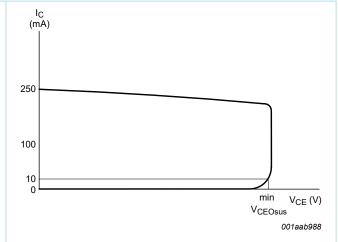
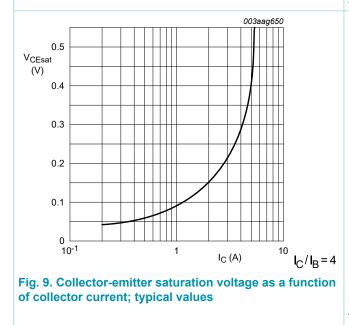
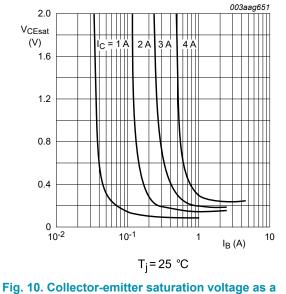


Fig. 8. Oscilloscope display for collector-emitter sustaining voltage test waveform



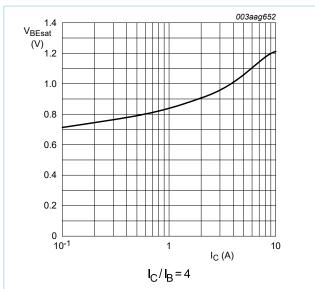




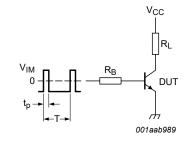
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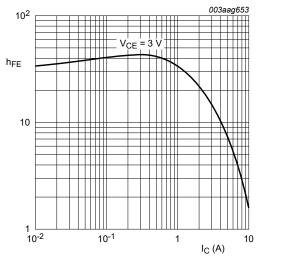
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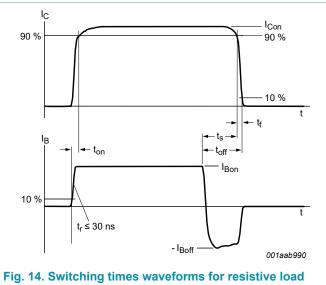


 $V_{IM} = -6$ to +8 V; $V_{CC} = 250$ V; $t_p = 20 \ \mu$ s; $\delta = \frac{t_p}{T} = 0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements. Fig. 13. Test circuit for resistive load switching





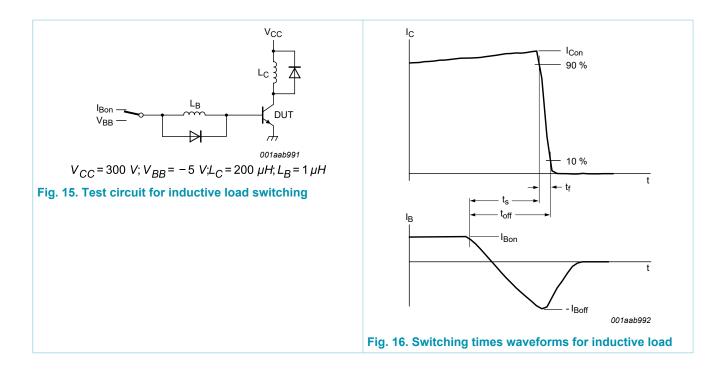




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11. Package outline

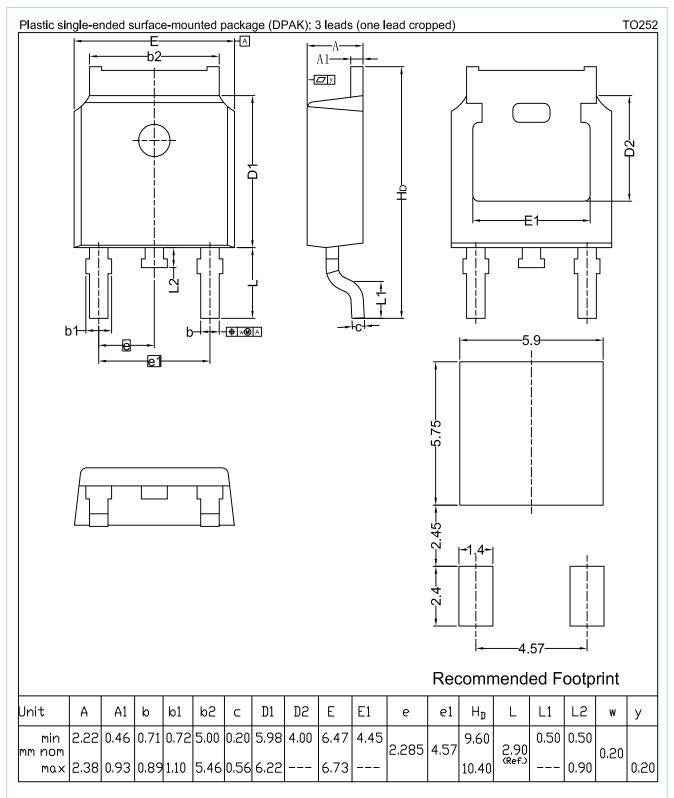


Fig. 17. Package outline DPAK (SOT428)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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